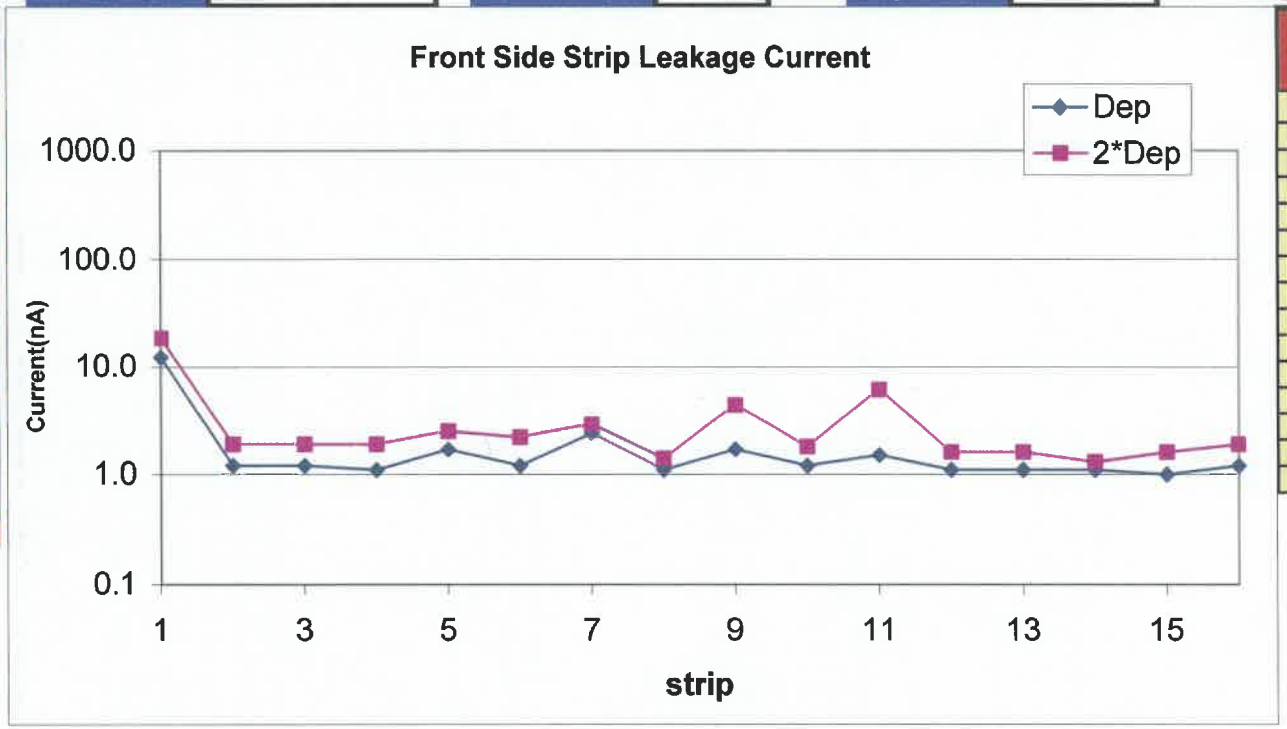
Detector Profile W1-60

Wafer No.: 2881-1 Thickness: 67 um Depletion: 10 Volts

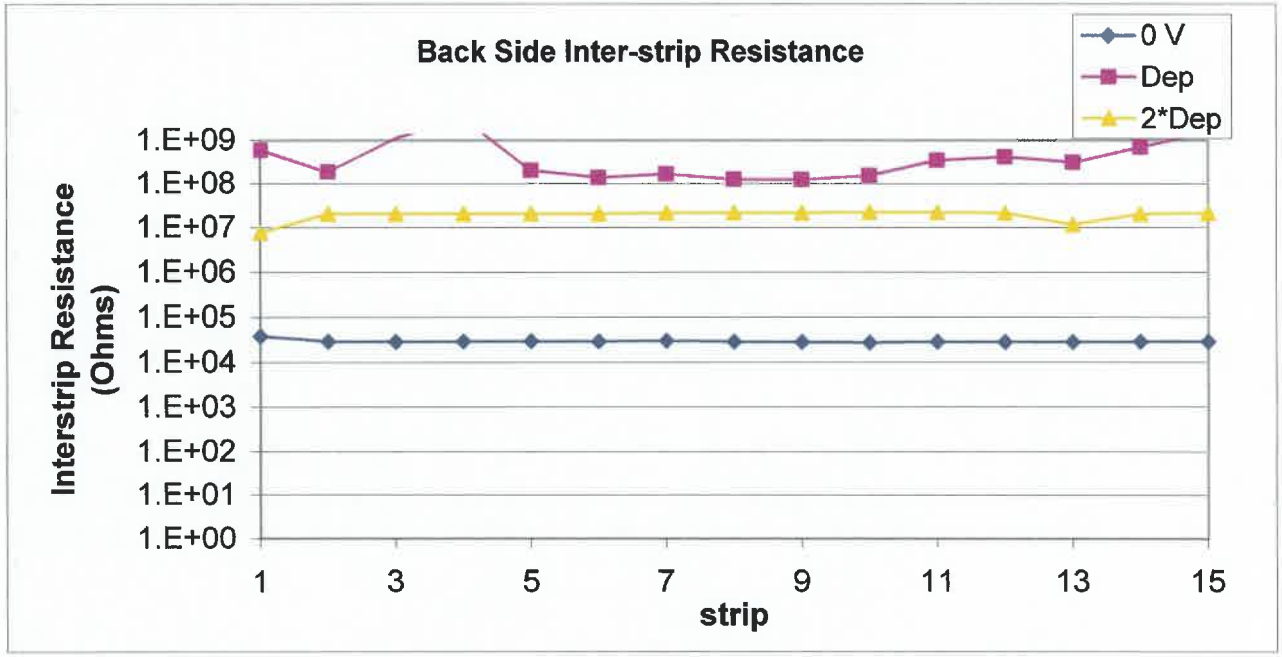
Front Side Data

Strip	Current(nA)	
	DEP.	2*Dep
1	12.30	18.60
2	1.20	1.90
3	1.20	1.90
4	1.10	1.90
5	1.70	2.50
6	1.20	2.20
7	2.40	2.90
8	1.10	1.40
9	1.70	4.40
10	1.20	1.80
11	1.50	6.10
12	1.10	1.60
13	1.10	1.60
14	1.10	1.30
15	1.00	1.60
16	1.20	1.90
total	32.10	53.60



Back Side Data

Strip	Back Resistance (Ω)		
	0V	DEP	2*Dep
1	3.8E+04	6.0E+08	7.7E+06
2	2.9E+04	1.9E+08	2.1E+07
3	2.9E+04	1.1E+09	2.1E+07
4	2.9E+04	3.2E+09	2.0E+07
5	3.0E+04	2.1E+08	2.1E+07
6	3.0E+04	1.4E+08	2.0E+07
7	3.0E+04	1.7E+08	2.2E+07
8	2.9E+04	1.3E+08	2.2E+07
9	2.8E+04	1.2E+08	2.2E+07
10	2.8E+04	1.5E+08	2.2E+07
11	2.9E+04	3.5E+08	2.2E+07
12	2.8E+04	4.2E+08	2.2E+07
13	2.8E+04	3.2E+08	1.2E+07
14	2.9E+04	7.0E+08	2.0E+07
15	2.9E+04	1.5E+09	2.2E+07

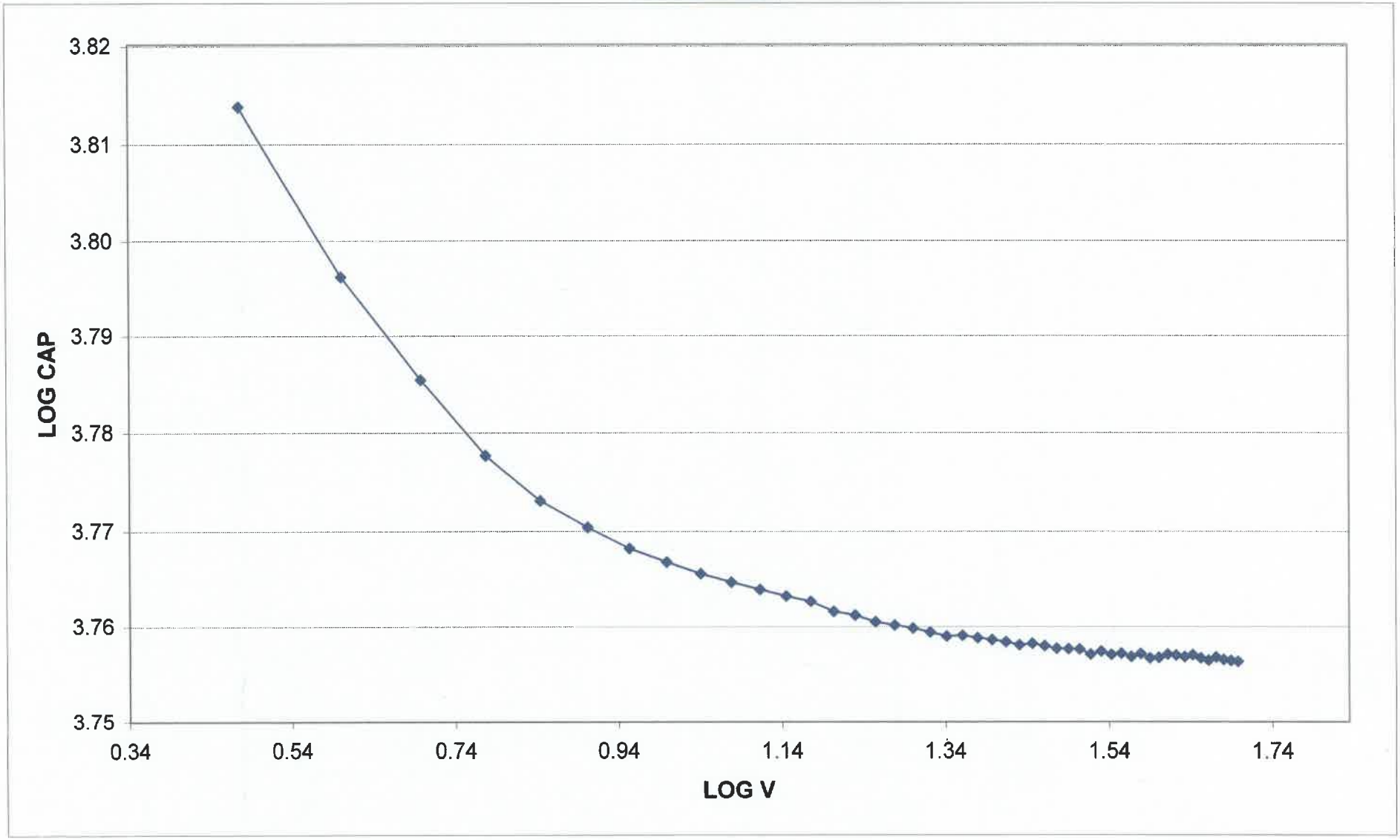


AARHUS UNIVERSITET
113491
AU.Reg.Nr.

Micron Semiconductor
22-03-11

Depletion Plot W1-60

Wafer No.:	2881-1	Thickness:	67 um
		Depletion:	10 Volts

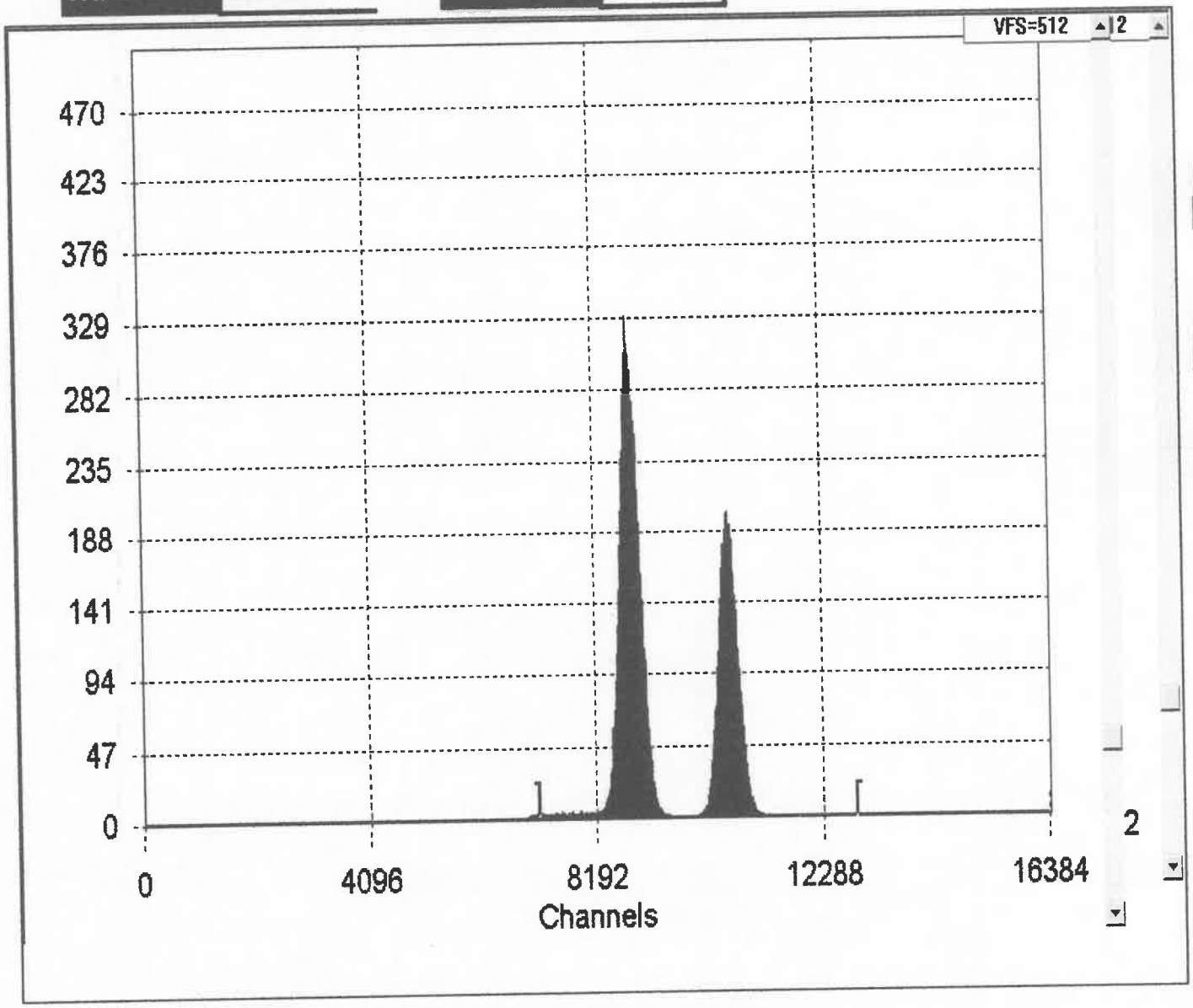


Micron Semiconductor
22-03-11

Resolution Plot

DESIGN W1(D/S) TYPE 9G

Wafer No.: **2881-1** Thickness: **67** um



Source: Am 241

Rise Time: 1

Flat Top: 0

JUNCTION

DET LINE: 176 KeV
SYSTEM: 142 KeV
CAL: 104 KeV

OHMIC

DET LINE: 180 KeV
SYSTEM: 142 KeV
CALC: 110 KeV

BIAS VOLTS= 20 V Leakage 35 nA

Micron Semiconductor
22/03/2011